L	Hits	Search Text	DB	Time stamp
Number				
241	0	recrysttalized near polysilicon	USPAT;	2004/07/25
			US-PGPUB;	23:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
242	189	recrystallized near polysilicon	USPAT;	2004/07/25
			US-PGPUB;	23:34
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
243	55	recrystallized near polysilicon near layer	USPAT;	2004/07/25
			US-PGPUB;	23:35
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
244	20	(recrystallized near polysilicon near layer)	USPAT;	2004/07/25
		and (gate adj electrode)	US-PGPUB;	23:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
245	6	(recrystallized near polysilicon near layer)	USPAT;	2004/07/25
		and (gate adj electrode) and capacitor	US-PGPUB;	23:37
			EPO; JPO;	
			DERWENT;	:
			IBM_TDB	
246	0	((recrystallized near polysilicon) near10	USPAT;	2004/07/25
		capacitor) and (gate adj electrode)	US-PGPUB;	23:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
247	0	((recrystallized near polysilicon) same	USPAT;	2004/07/25
		capacitor) and (gate adj electrode)	US-PGPUB;	23:36
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
248	3	(recrystallized near polysilicon).clm. and	USPAT;	2004/07/25
		(gate adj electrode) and capacitor	US-PGPUB;	23:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
249	4	(recrystallized near polysilicon).clm. and	USPAT;	2004/07/25
		(gate).clm. and capacitor	US-PGPUB;	23:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
250	1	(recrystallized near polysilicon).clm. and	USPAT;	2004/07/25
		(gate).clm. and capacitor.clm.	US-PGPUB;	23:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	•

251	1	(recrystallized adj polysilicon).ti,ab,clm.	USPAT;	2004/07/25
		and (gate).clm. and capacitor.clm.	US-PGPUB;	23:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
252	1	(recrystallized adj polysilicon).ti,ab,clm.	USPAT;	2004/07/25
		and (gate).clm. and capacitor.ti,ab,clm.	US-PGPUB;	23:40
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
253	2	(recrystallized adj polysilicon).ti,ab,clm.	USPAT;	2004/07/25
		and (gate).ti,ab,clm. and	US-PGPUB;	23:52
		capacitor.ti,ab,clm.	EPO; JPO;	
		. ,	DERWENT;	
			IBM_TDB	
254	23	(recrystallized adj polysilicon) and	USPAT;	2004/07/25
		(gate).ti,ab,clm. and capacitor.ti,ab,clm.	US-PGPUB;	23:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
255	162	recrystallized adj polysilicon	USPAT;	2004/07/25
			US-PGPUB;	23:53
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
256	4	(recrystallized adj polysilicon) near10 (gate	USPAT;	2004/07/25
	1	adj electrode)	US-PGPUB;	23:53
		· ·	EPO; JPO;	
			DERWENT;	
			IBM TDB	